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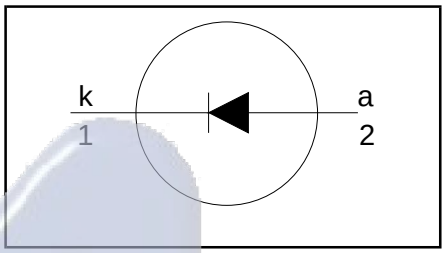
Rectifier diodes ultrafast

BYV29 series

FEATURES

- Low forward volt drop
- Fast switching
- Soft recovery characteristic
- High thermal cycling performance
- Low thermal resistance

SYMBOL



QUICK REFERENCE DATA

V_R = 300 V/ 400 V/ 500 V

$V_F \leq 1.03$ V

$I_{F(AV)}$ = 9 A

$t_{rr} \leq 60$ ns

GENERAL DESCRIPTION

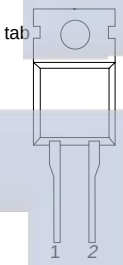
Ultra-fast, epitaxial rectifier diodes intended for use as output rectifiers in high frequency switched mode power supplies.

The BYV29 series is supplied in the conventional leaded SOD59 (TO220AC) package.

PINNING

PIN	DESCRIPTION
1	cathode
2	anode
tab	cathode

SOD59 (TO220AC)



LIMITING VALUES

Limiting values in accordance with the Absolute Maximum System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.			UNIT
		BYV29		-300	-400	-500	
V_{RRM}	Peak repetitive reverse voltage		-	300	400	500	V
V_{RWM}	Crest working reverse voltage		-	300	400	500	V
V_R	Continuous reverse voltage		-	300	400	500	V
$I_{F(AV)}$	Average forward current[1]	square wave; δ = 0.5; $T_{mb} \leq 123$ ˚C	-		9		A
I_{FRM}	Repetitive peak forward current	t = 25 µs; δ = 0.5; $T_{mb} \leq 123$ ˚C	-		18		A
I_{FSM}	Non-repetitive peak forward current.	t = 10 ms	-		100		A
		t = 8.3 ms sinusoidal; with reapplied $V_{RRM(max)}$	-		110		A
T_{stg}	Storage temperature		-40		150		˚C
T_j	Operating junction temperature		-		150		˚C

THERMAL RESISTANCES

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$R_{th\ j\text{-}mb}$	Thermal resistance junction to mounting base		-	-	2.5	K/W
$R_{th\ j\text{-}a}$	Thermal resistance junction to ambient	in free air.	-	60	-	K/W

1 Neglecting switching and reverse current losses.

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ELECTRICAL CHARACTERISTICS

T_j = 25 ˚C unless otherwise stated

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	Forward voltage	I_F = 8 A; T_j = 150˚C	-	0.90	1.03	V
		I_F = 8 A	-	1.05	1.25	V
		I_F = 20 A	-	1.20	1.40	V
I_R	Reverse current	$V_R = V_{RRM}$	-	2.0	50	µA
		$V_R = V_{RRM}$; T_j = 100 ˚C	-	0.1	0.35	mA
Q_s	Reverse recovery charge	I_F = 2 A to $V_R \geq$ 30 V; dI_F/dt = 20 A/µs	-	40	60	nC
t_{rr}	Reverse recovery time	I_F = 1 A to $V_R \geq$ 30 V; dI_F/dt = 100 A/µs	-	50	60	ns
I_{rrm}	Peak reverse recovery current	I_F = 10 A to $V_R \geq$ 30 V; dI_F/dt = 50 A/µs; T_j = 100˚C	-	4.0	5.5	A
V_{fr}	Forward recovery voltage	I_F = 10 A; dI_F/dt = 10 A/µs	-	2.5	-	V

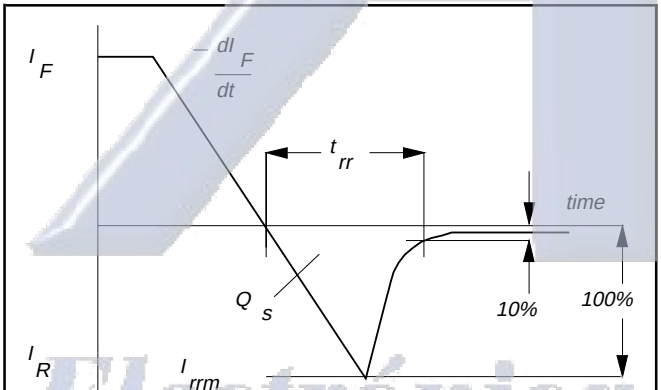

Fig.1. Definition of t_{rr}, Q_s and I_{rrm}

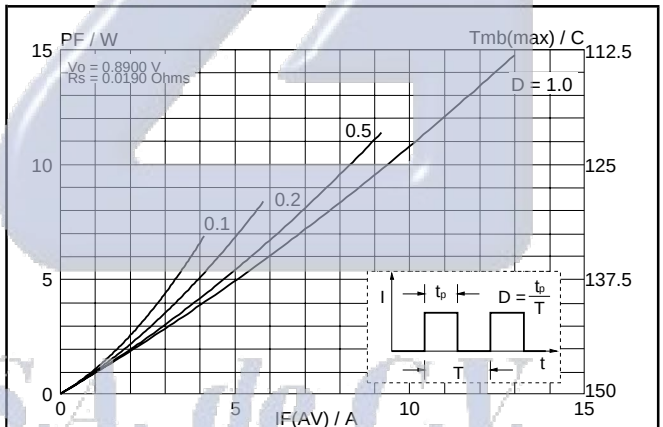

Fig.3. Maximum forward dissipation $P_F = f(I_{F(AV)})$; square wave where $I_{F(AV)} = I_{F(RMS)} \times \sqrt{D}$.

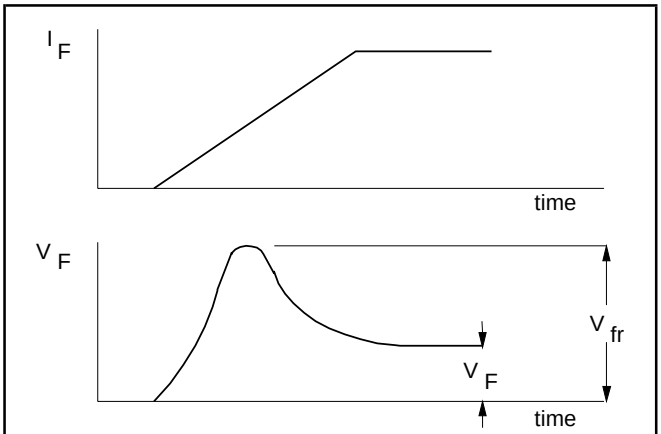

Fig.2. Definition of V_{fr}

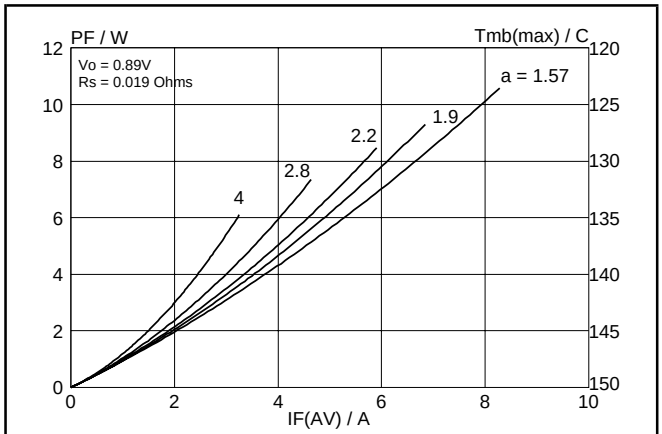

Fig.4. Maximum forward dissipation $P_F = f(I_{F(AV)})$; sinusoidal current waveform where a = form factor = $I_{F(RMS)} / I_{F(AV)}$.

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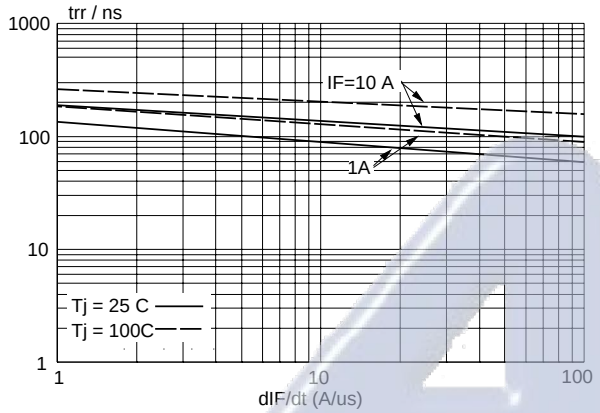

Fig.5. Maximum t_{rr} at T_j = 25˚C and 100˚C

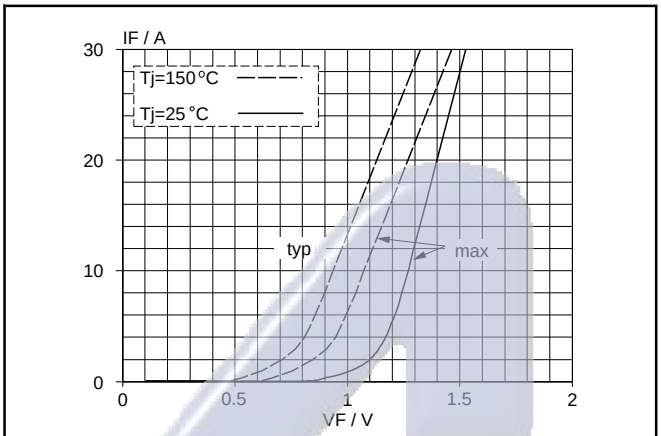

Fig.7. Typical and maximum forward characteristic $I_F = f(V_F)$; parameter T_j

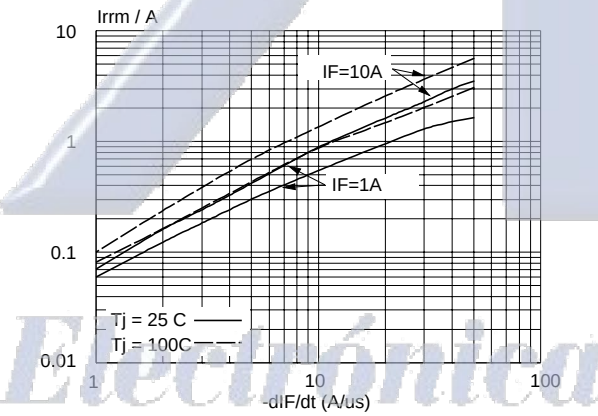

Fig.6. Maximum I_{rrm} at T_j = 25˚C and 100˚C.

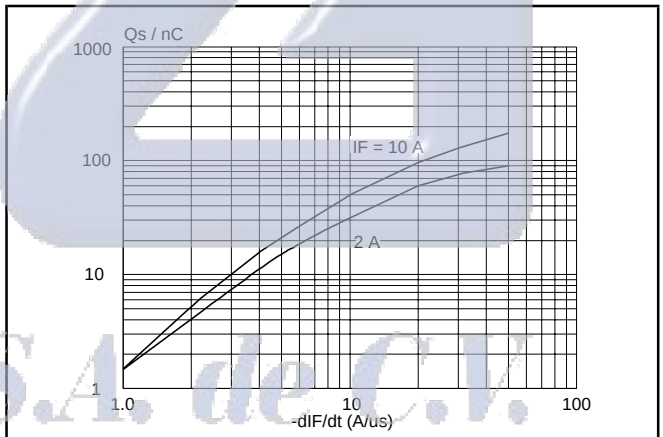

Fig.8. Maximum Q_s at T_j = 25˚C

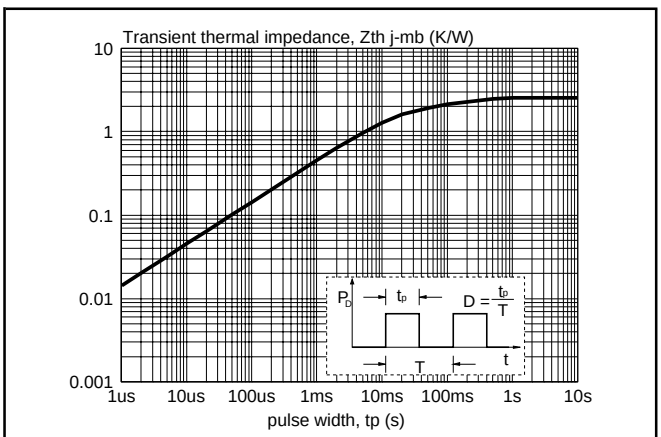

Fig.9. Transient thermal impedance $Z_{th\ j\text{-}mb}$= f(t_p)

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MECHANICAL DATA

Dimensions in mm

Net Mass: 2 g

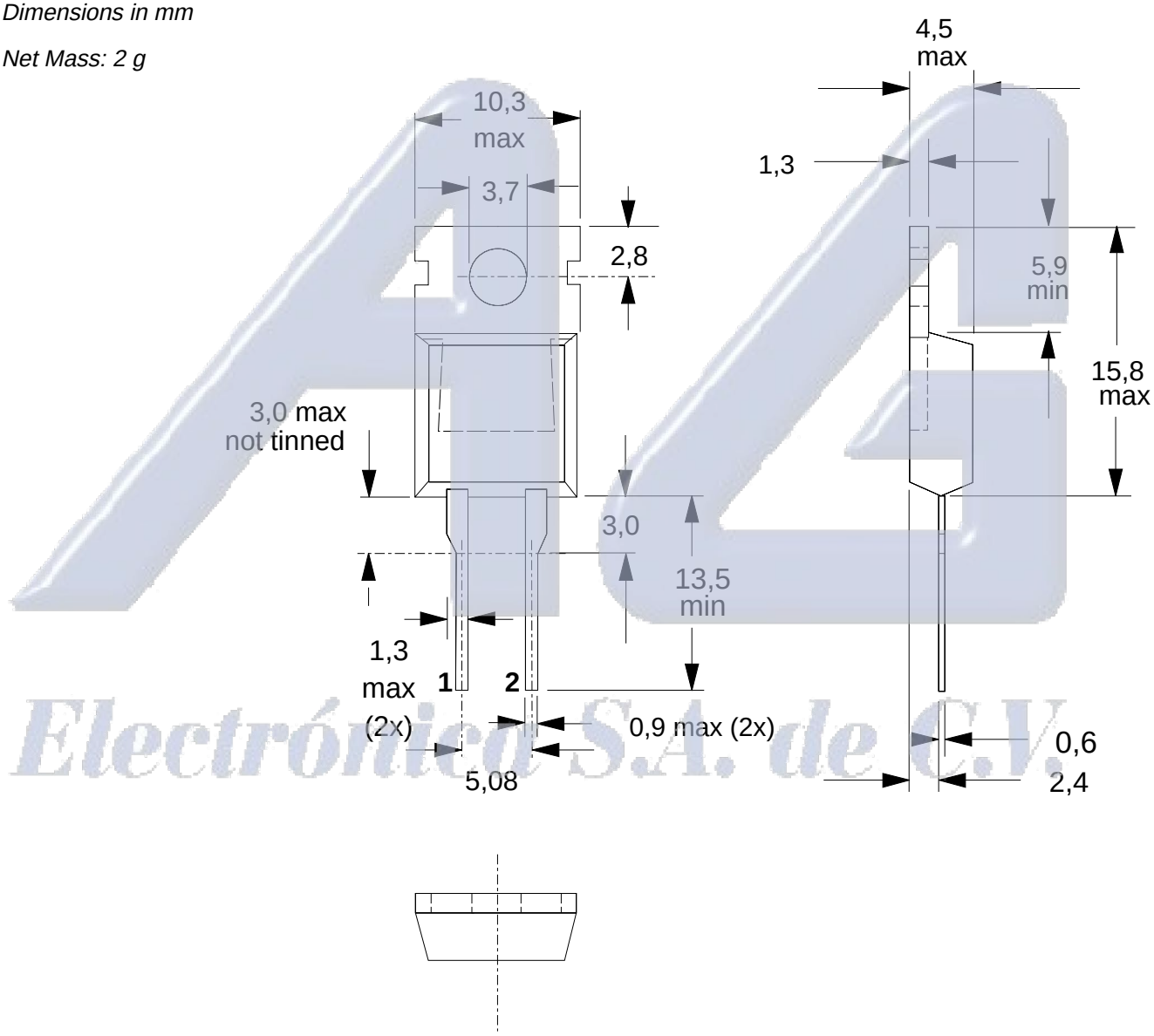

Fig.10. SOD59 (TO220AC). pin 1 connected to mounting base.

Notes
1. Refer to mounting instructions for TO220 envelopes.
2. Epoxy meets UL94 V0 at 1/8".

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